- 1.(Original) A method for manufacturing a Thin Film

 Inorganic Light Emitting Diode device, said method

 comprising the following steps, in order,:
 - (1) preparing a nanoparticle dispersion of ZnS doped with a luminescent centre by precipitation from appropriate aqueous solutions comprising zinc ions, sulfide ions and dopant ions,
 - (2) washing said dispersion of doped ZnS to remove nonprecipitated ions,
 - (3) coating onto a first conductive electrode said washed dispersion of doped ZnS, optionally after admixture with a binder,
 - (4) applying on top of said coated layer resulting from step (3) a second conductive electrode, with the proviso that at least one of said first and second electrode is transparent.
- 2.(Original) A method according to claim 1 wherein said precipitation of step (1) is performed according to the double jet principle whereby a first solution containing zinc ions and a second solution containing sulfide ions are added together to a third solution.

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- 3. (Original) A method according to claim 2 wherein said first solution also contains said dopant ions.
- 4. (Original) A method according to claim 1 wherein said dopant ions are Cu^{2+} ions.
- 5. (Original) A method according to claim 1 wherein said dopant ions are Cu^+ ions.
- 6. (Original) A method according to claim 1 wherein said dopant ions are Mn^{2+} ions.
- 7. (Currently Amended) A method Method according to claims

 claim 1 wherein said washing of said dispersion of doped

 ZnS is performed by an ultrafiltration step,

 ultrafiltration step and a diafiltration step, or a

 and/or diafiltration step.
- 8. (Currently Amended) A method Method according to claim 7 wherein said ultrafiltration step, ultrafiltration step and a diafiltration step, or a and/or diafiltration step is (are) performed in the presence of a compound preventing agglomeration of nanoparticles.
- 9. (Original) A method according to claim 8 wherein said compound preventing the agglomeration of nanoparticles is a polyphosphate or polyphosphoric acid.
- 10. (Original) A method according to claim 1 wherein said first electrode is an Indium Tin Oxide (ITO) electrode.

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- 11. (Original) A method according to claim 1 wherein said first electrode is a foil comprising a polythiophene/polyanion complex.
- 12. (Original) A method according to claim 11 wherein said polythiophene/polyanion complex is a poly(3,4-ethylenedioxythiophene) polystyrene sulphonate complex.
- 13. (Original) A method according to claim 1 wherein said second conductive electrode is an aluminum electrode applied by vacuum deposition.
- 14. (Currently Amended) A Thin Film Inorganic Light Emitting

 Diode device manufactured according to the a method of

 any of the previous claims for manufacturing a Thin Film

 Inorganic Light Emitting Diode device, said method

 comprising the following steps, in order:
 - (1) preparing a nanoparticle dispersion of ZnS doped with a luminescent center by precipitation from appropriate aqueous solutions comprising zinc ions, sulfide ions and dopant ions
 - (2) washing said dispersion of doped ZnS to remove nonprecipitated ions,
 - (3) coating onto a first conductive electrode said washed dispersion of doped ZnS optionally after admixture with a binder, and



(4) applying on top of said coated layer resulting from step (3) a second conductive electrode, with the proviso that at least one of said first and second electrodes is transparent.